

KEC

SEMICONDUCTOR
TECHNICAL DATA

KHB4D0N80P1/F1/F2

N CHANNEL MOS FIELD
EFFECT TRANSISTOR

General Description

This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for electronic ballast and switch mode power supplies.

FEATURES

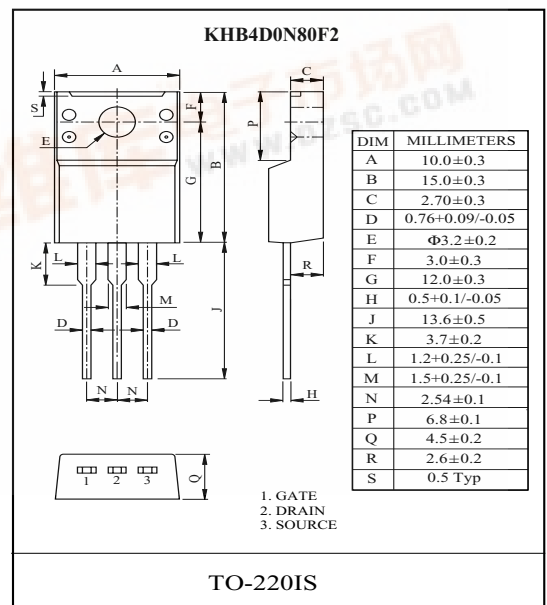
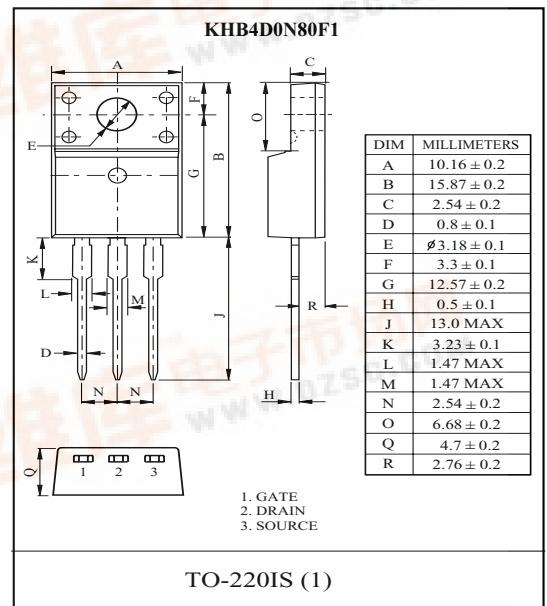
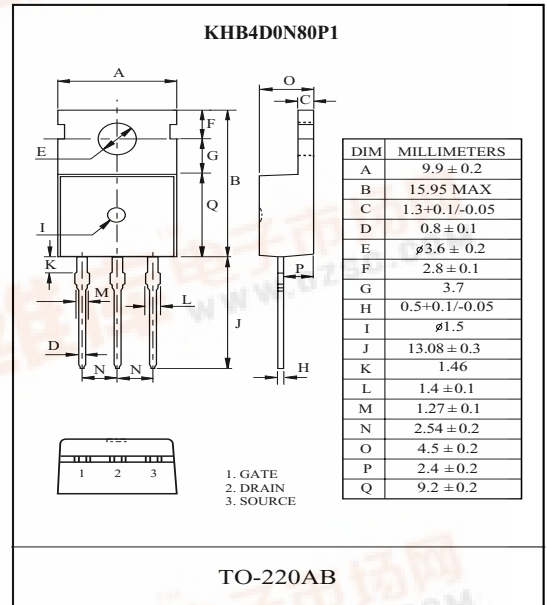
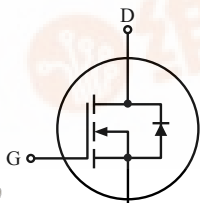
- $V_{DSS}=800V$, $I_D=4A$
- Drain-Source ON Resistance
: $R_{DS(ON)}=3.6\ \Omega$ @ $V_{GS}=10V$
- $Q_g(\text{typ.})=25nC$

MAXIMUM RATING (Tc=25℃)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			KHB4D0N80P1	KHB4D0N80F1 KHB4D0N80F2	
Drain-Source Voltage		V _{DSS}	800		V
Gate-Source Voltage		V _{GSS}	±30		V
Drain Current	@T _C =25℃	I _D	4.0	4.0*	A
	Pulsed (Note1)	I _{DP}	16	16*	
Single Pulsed Avalanche Energy (Note 2)		E _{AS}	460		mJ
Repetitive Avalanche Energy (Note 1)		E _{AR}	13		mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.0		V/ns
Drain Power Dissipation	Tc=25℃	P _D	130	43	W
	Derate above25℃		1.04	0.34	W/℃
Maximum Junction Temperature		T _j	150		℃
Storage Temperature Range		T _{stg}	-55~150		℃
Thermal Characteristics					
Thermal Resistance, Junction-to-Case		R _{thJC}	0.96	2.9	℃/W
Thermal Resistance, Junction-to-Ambient		R _{thJA}	62.5	62.5	℃/W

* : Drain current limited by maximum junction temperature.

PIN CONNECTION



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ELECTRICAL CHARACTERISTICS (Tc=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	800	-	-	V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} / ΔT _j	I _D =250μA, Referenced to 25 °C	-	0.95	-	V/°C
Gate Threshold Voltage	V _{th}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Drain Cut-off Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V,	-	-	10	μA
Gate Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.0A	-	3.0	3.6	Ω
Forward Transconductance	g _{FS}	V _{DS} =50V, I _D =2.0A (Note4)	-	3.8	-	S
Dynamic						
Total Gate Charge	Q _g	V _{DS} =640V, I _D =4.0A V _{GS} =10V (Note4, 5)	-	25	31	nC
Gate-Source Charge	Q _{gs}		-	4	-	
Gate-Drain Charge	Q _{gd}		-	13	-	
Turn-on Delay time	t _{d(on)}	V _{DD} =400V, R _G =25 Ω I _D =4.0A (Note4, 5)	-	29.5	69	ns
Turn-on Rise time	t _r		-	59.5	129	
Turn-off Delay time	t _{d(off)}		-	98	206	
Turn-off Fall time	t _f		-	86	182	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	824	1071	pF
Output Capacitance	C _{oss}		-	68	88	
Reverse Transfer Capacitance	C _{rss}		-	9	12	
Source-Drain Diode Ratings						
Continuous Source Current	I _S	V _{GS} <V _{th}	-	-	4.0	A
Pulsed Source Current	I _{SP}		-	-	16	
Diode Forward Voltage	V _{SD}	I _S =4.0A, V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time	t _{rr}	I _S =4.0A, V _{GS} =0V,	-	575	-	ns
Reverse Recovery Charge	Q _{rr}	dI _S /dt=100A/μs (Note 4)	-	3.65	-	μC

Note 1) Repetivity rating : Pulse width limited by junction temperature.

Note 2) $L=54mH$, $I_S=4A$, $V_{DD}=50V$, $R_G=25\Omega$, Starting $T_j=25^\circ C$.

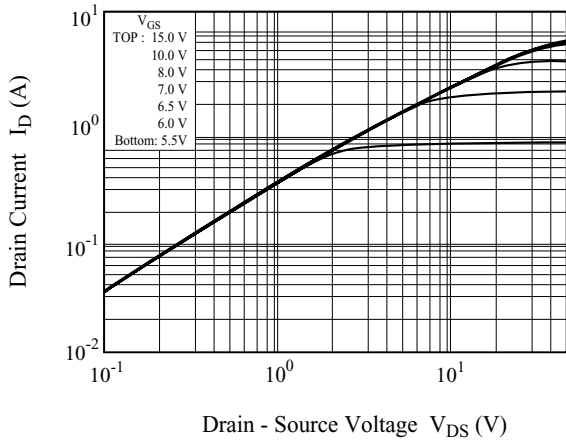
Note 3) $I_S \leq 4.0A$, $dI/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_j=25^\circ C$.

Note 4) Pulse Test : Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

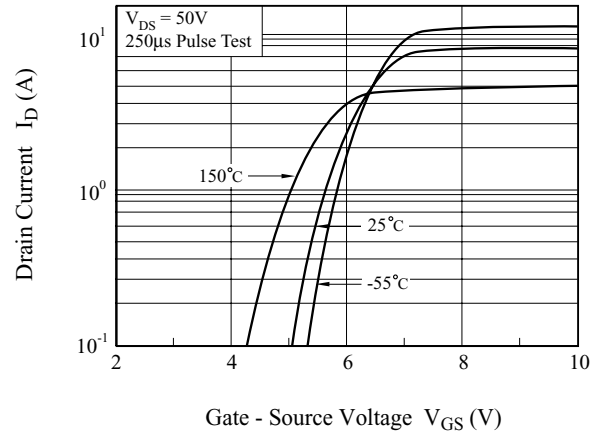
Note 5) Essentially independent of operating temperature.

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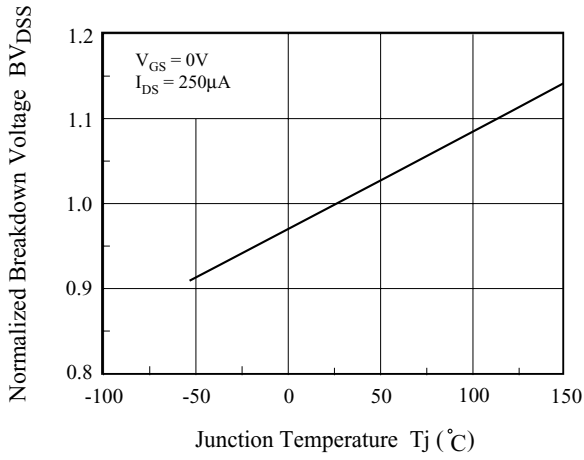
$I_D - V_{DS}$



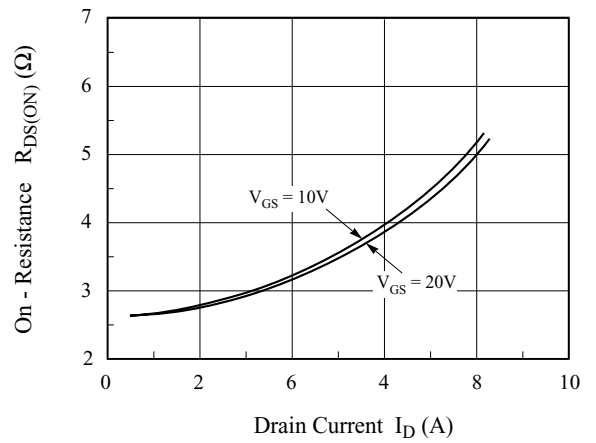
$I_D - V_{GS}$



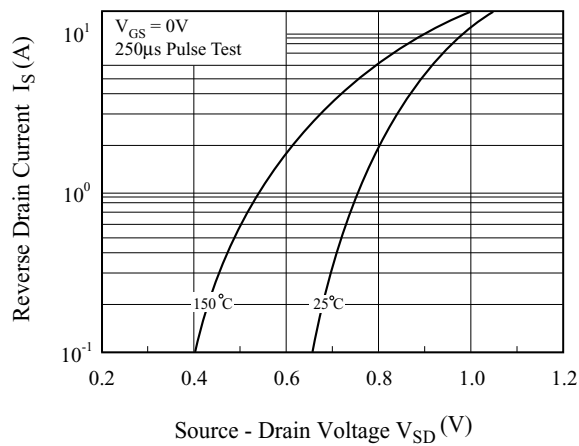
$BV_{DSS} - T_j$



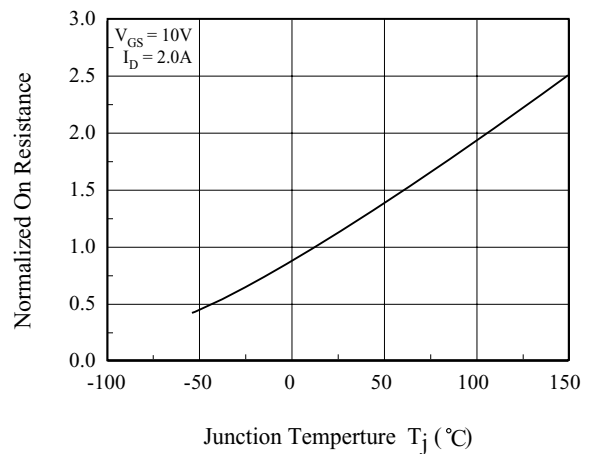
$R_{DS(ON)} - I_D$



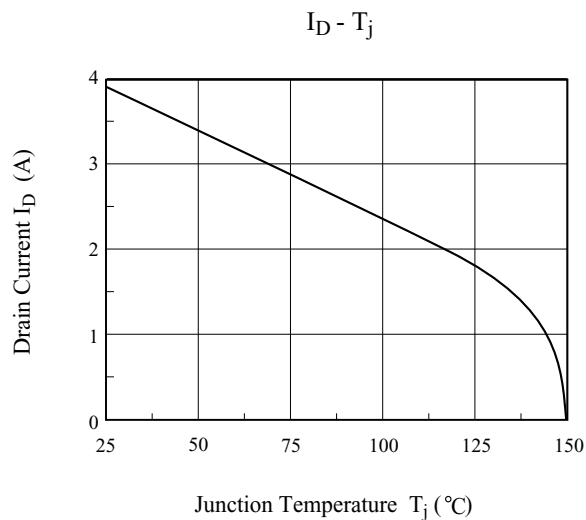
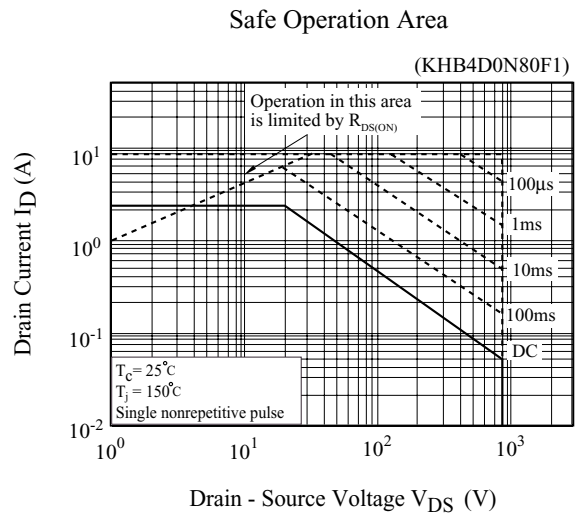
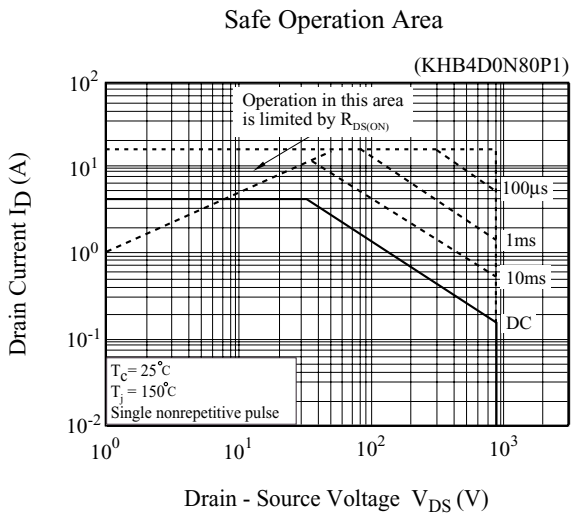
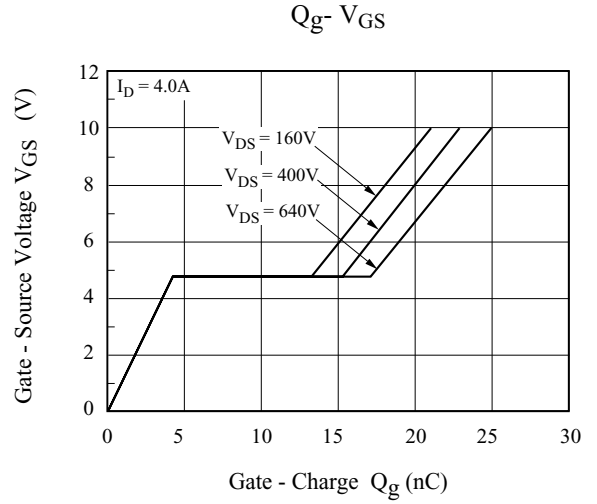
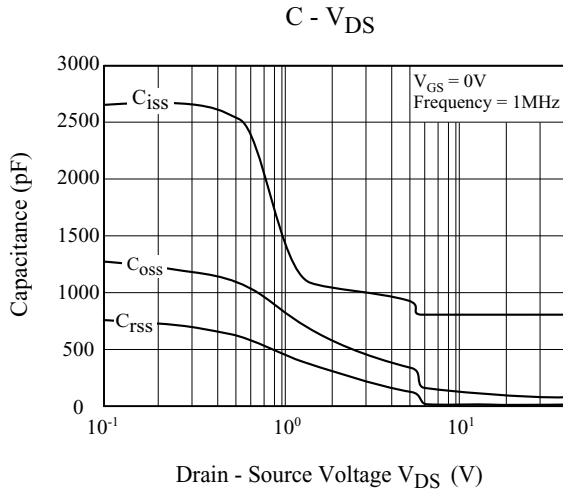
$I_S - V_{SD}$



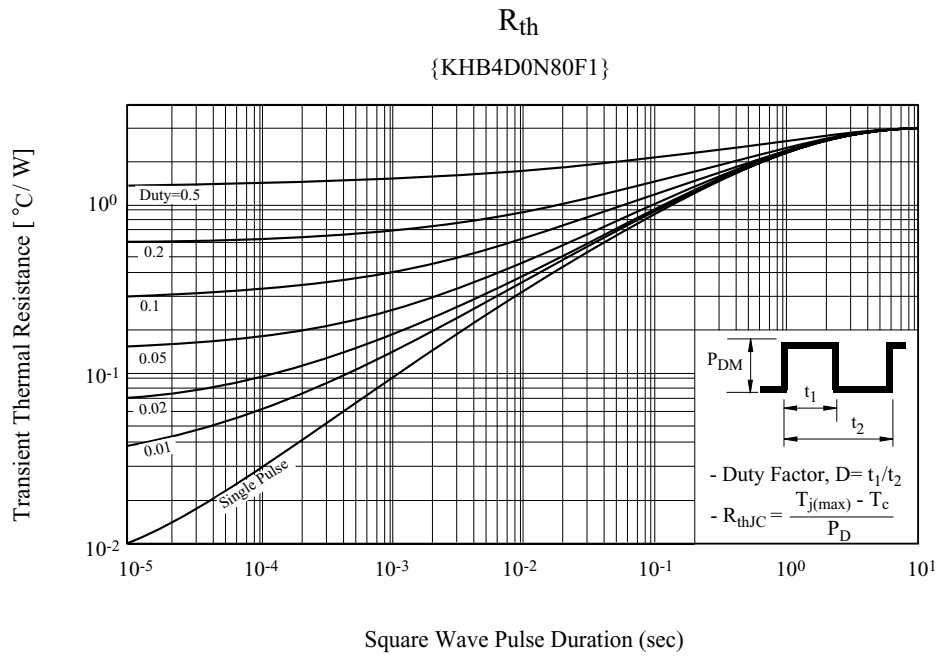
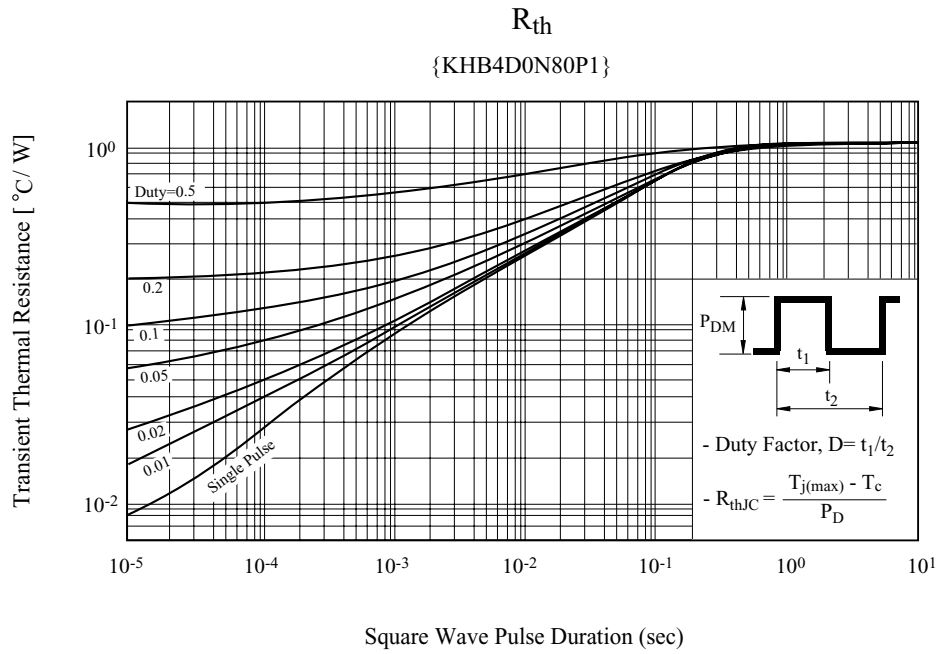
$R_{DS(ON)} - T_j$



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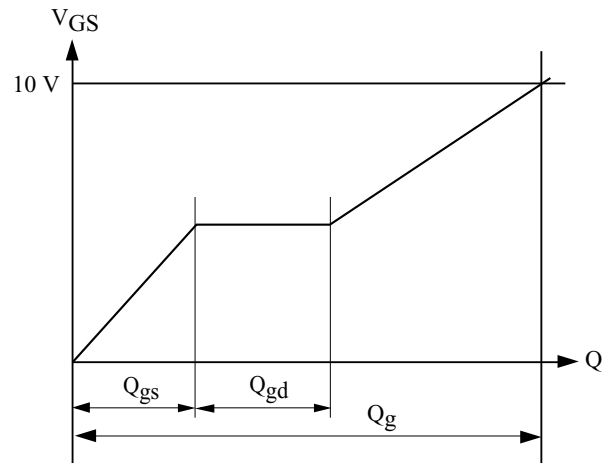
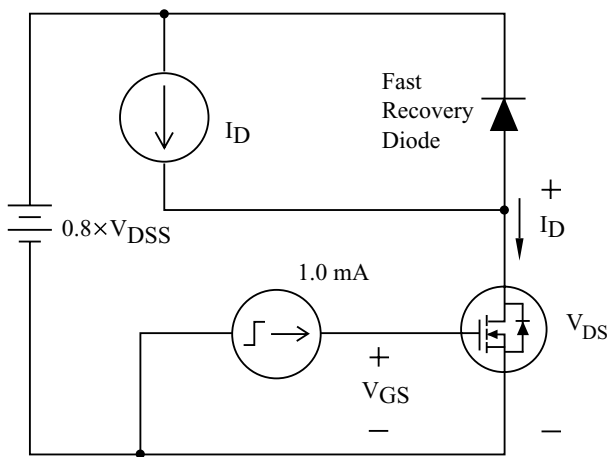


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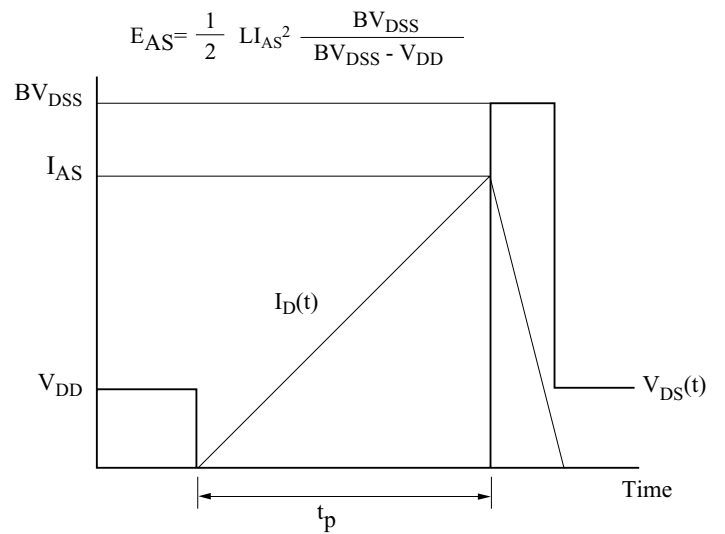
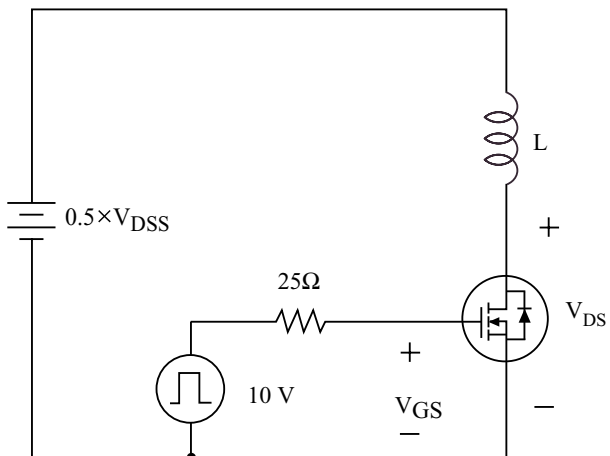


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- Gate Charge

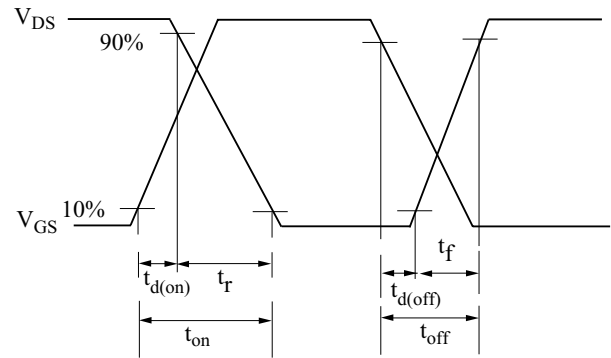
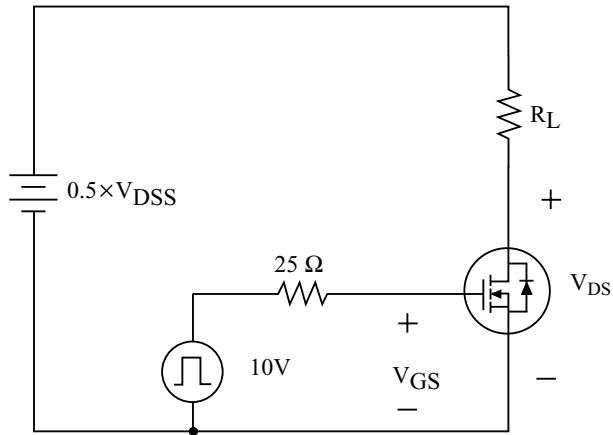


- Single Pulsed Avalanche Energy



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- Resistive Load Switching



- Source - Drain Diode Reverse Recovery and dv/dt

